

MBRB2545CT SCHOTTKY RECTIFIER

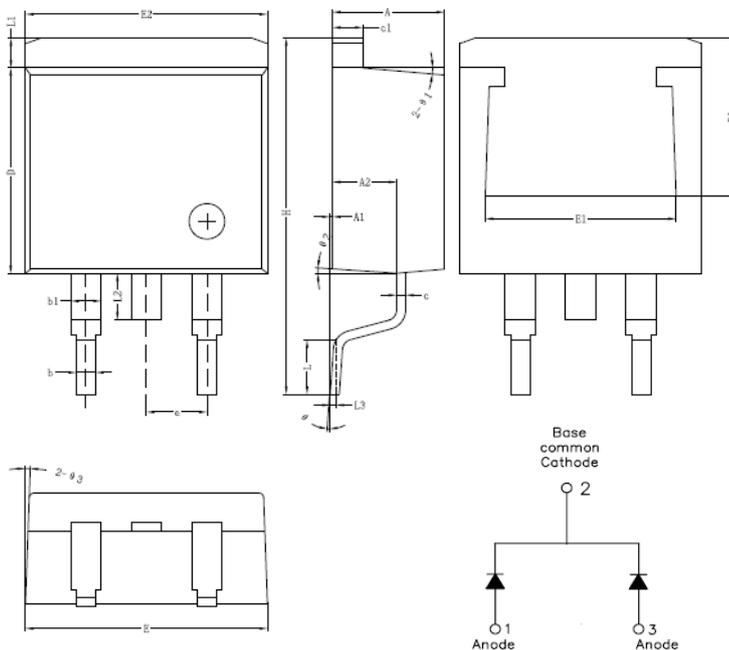
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 200°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Pure tin plated, solderable per MIL-STD-750, Method 2026
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

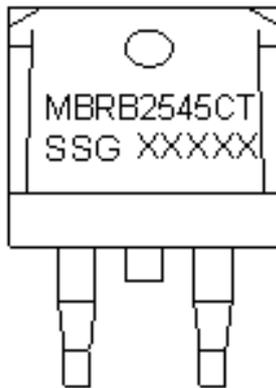
Mechanical Dimensions (In mm):



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

D² PAK

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Marking Diagram:


Where XXXXX is YYWWL

MBR	= Device Type
B	= Package type
25	= Forward Current (25A)
45	= Reverse Voltage (45V)
CT	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRB2545CT	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	45	V
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
Average Rectified Forward Current (per device)	$I_{F(AV)}$	50% duty cycle @ $T_C = 130^\circ\text{C}$, rectangular wave form	25	A
Peak One Cycle Non-Repetitive Surge Current(per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg)*	V_{F1}	@ 12.5 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.56	0.70	V
	V_{F2}	@ 12.5 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.54	0.60	V
Reverse Current (per leg)*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	0.03	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_C = 125\text{ }^\circ\text{C}$	15	40	mA
Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	300	800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature at reduced reverse voltage at reduced reverse voltage in DC forward mode	T_J	$V_R \leq 80\%V_{RRM}$ $V_R \leq 50\%V_{RRM}$	-55 to +150 -55 to +180 -55 to +200	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	4.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.85	g
Case Style	D2PAK(TO-263AB)			

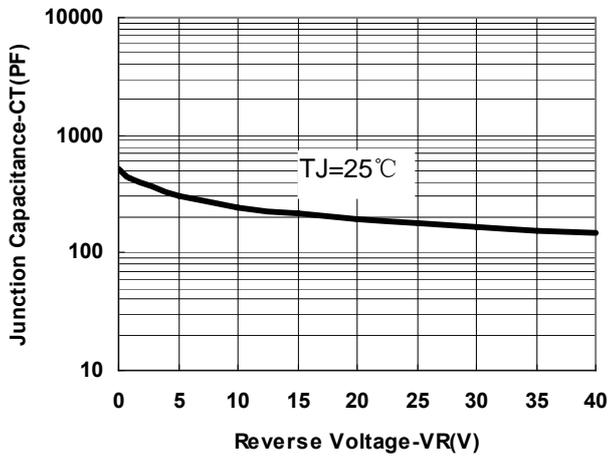


Fig.1-Typical Junction Capacitance

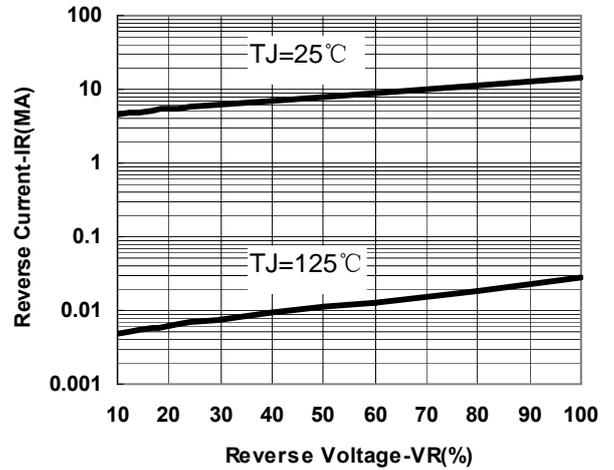


Fig.2-Typical Reverse Characteristics

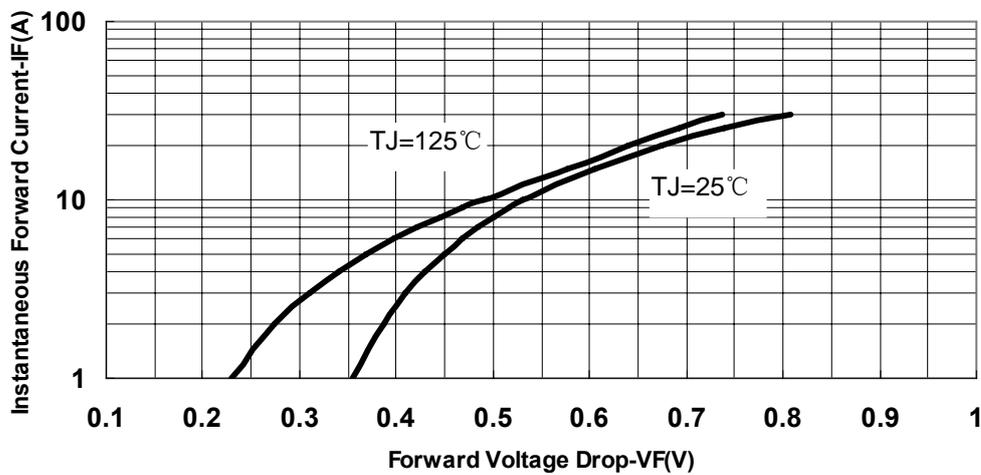


Fig.3-Typical Forward Voltage Drop Characteristics



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